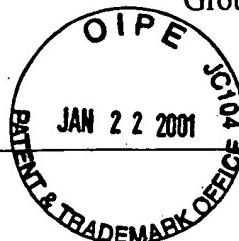


IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Hsiao, Tommy C.; Hui, Angela T.; Ogle, Robert B.; Pham, Tuan Duc;
Plat, Marina V.; Ramsbey, Mark T.; Shen, Lewis
Assignee: Advanced Micro Devices, Inc.
Title: Polished Flash Process With Metal Gates And Improved Planarity
Serial No.: 09/430,366 Filing Date: October 28, 1999
Examiner: J. Chen Group Art Unit: 2813
Docket No.: M-7523 US



6th/Jan/2001
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January 16, 2001

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COMMISSIONER FOR PATENTS
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AMENDMENT

Dear Sir:

This submission responds to the Office Action of July 7, 2000. Applicants amend the above-referenced patent application as follows:

IN THE CLAIMS

Please cancel Claim 13.

Please amend Claims 1-5 and 7-11 as follows:]

1. (Amended) A method of making a flash memory cell including a substrate [having] and a floating gate [of a first thickness], the method comprising:
forming an oxide on exposed surfaces of the floating gate; → Not shown in drawing
depositing an insulator layer on the substrate[, the insulator covering] and the floating gate, the insulator layer being deposited to a thickness greater than a thickness

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